

HZU Series

Silicon Planar Zener Diode for Stabilizer

REJ03G0625-0900 Rev.9.00 Jul 06, 2006

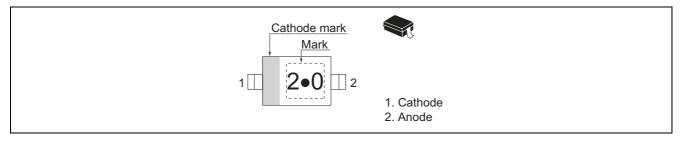
Features

- These diodes are delivered taped.
- Ultra small Resin Package (URP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Name	Package Code		
HZU Series	Let to Mark Code	URP	PTSP0002ZA-A		

Pin Arrangement





Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Symbol	Value	Unit	
Pd * ¹	200	mW	
Тј	150	°C	
Tstg	-55 to +150	°C	
	Pd * ¹ Tj	Pd *1 200 Tj 150	

Note: 1. With P.C. Board.

Electrical Characteristics

	1				<u> </u>			$(Ta = 25^{\circ}C)$
		Zener Voltage			Rever	se Current	Dynamic Resistance	
			a a +1	Test		Test	(0)	Test
_			(V)* ¹	Condition	I _R (∝A)	Condition	r _d (Ω)	Condition
Туре	Grade	Min	Max	I _Z (mA)	Max	V _R (V)	Max	I _Z (mA)
HZU2.0	B	1.90	2.20	5	120	0.5	100	5
HZU2.2	В	2.10	2.40	5	120	0.7	100	5
HZU2.4	В	2.30	2.60	5	120	1.0	100	5
HZU2.7	В	2.50	2.90	5	120	1.0	110	5
	B1	2.50	2.75					
	B2	2.65	2.90					
HZU3.0	В	2.80	3.20	5	50	1.0	120	5
	B1	2.80	3.05					
	B2	2.95	3.20					
HZU3.3	В	3.10	3.50	5	20	1.0	130	5
	B1	3.10	3.35					
	B2	3.25	3.50					
HZU3.6	В	3.40	3.80	5	10	1.0	130	5
	B1	3.40	3.65					
	B2	3.55	3.80					
HZU3.9	В	3.70	4.10	5	10	1.0	130	5
	B1	3.70	3.97					
	B2	3.87	4.10					
HZU4.3	В	4.01	4.48	5	10	1.0	130	5
	B1	4.01	4.21					
	B2	4.15	4.34					
	B3	4.28	4.48					
HZU4.7	В	4.42	4.90	5	10	1.0	130	5
	B1	4.42	4.61					
	B2	4.55	4.75					
	B3	4.69	4.90					
HZU5.1	В	4.84	5.37	5	5	1.5	130	5
	B1	4.84	5.04	1	-			
	B2	4.98	5.20	1				
	B3	5.14	5.37	-				
HZU5.6	B	5.31	5.92	5	5	2.5	80	5
	B1	5.31	5.55	1 -				-
	B2	5.49	5.73	1				
	B3	5.67	5.92	1				

Note: 1. Tested with pulse ($P_W = 40 \text{ ms}$)



			Zener Voltage			se Current	Dynamic Resistance	
		V7 ((V)* ¹	Test Condition	I _R (∝A)	Test Condition	r _d (Ω)	Test Condition
Туре	Grade	Min	Max	l _z (mA)	Max	V _R (V)	Max	I _Z (mA)
HZU6.2	В	5.86	6.53	5	2	3.0	50	5
	B1	5.86	6.12					
	B2	6.06	6.33					
	B3	6.26	6.53	-				
HZU6.8	В	6.47	7.14	5	2	3.5	30	5
	B1	6.47	6.73					
	B2	6.65	6.93	-				
	B3	6.86	7.14	-				
HZU7.5	B	7.06	7.84	5	2	4.0	30	5
	B1	7.06	7.36	-	_			-
	B2	7.28	7.60					
	B3	7.52	7.84					
HZU8.2	B	7.76	8.64	5	2	5.0	30	5
	B1	7.76	8.10	1	_			
	B2	8.02	8.36	1				
	B3	8.28	8.64	-				
HZU9.1	B	8.56	9.55	5	2	6.0	30	5
-	 B1	8.56	8.93	Ŭ	-	0.0	00	Ũ
	B2	8.85	9.23	-				
	B3	9.15	9.55	-				
HZU10	B	9.45	10.55	5	2	7.0	30	5
112010	B1	9.45	9.87		<u> </u>	7.0	00	J J
	B2	9.77	10.21	-				
	B2 B3	10.11	10.55	-				
HZU11	B	10.44	11.56	5	2	8.0	30	5
112011	B1	10.44	10.88		<u> </u>	0.0	00	5
	B1 B2	10.76	11.22	-				
	B2 B3	11.10	11.56	-				
HZU12	B	11.42	12.60	5	2	9.0	35	5
112012	B1	11.42	11.90	5	2	3.0	55	5
	B1 B2	11.74	12.24	-				
	B2 B3	12.08	12.60					
HZU13	B	12.00	13.96	5	2	10.0	35	5
	B1	12.47	13.96		<u>د</u>	10.0	55	5
	B1 B2	12.47	13.03	4				
	B2 B3	13.37	13.49	4				
HZU15	B	13.37	15.52	5	2	11.0	40	5
	B1	13.84	15.52	5	۷	11.0	40	5
	B1 B2	13.84		4				
			14.98	-				
HZU16	B3 B	14.85 15.37	15.52 17.09	E	0	10.0	40	5
	B1	15.37		5	2	12.0	40	5
			16.01	-				
	B2	15.58	16.51	4				
	B3	16.35	17.09	-		10.0	4-	-
HZU18	B	16.94	19.03	5	2	13.0	45	5
	B1	16.94	17.70	4				
	B2	17.56	18.35	4				
	B3	18.21	19.03					

Note: 1. Tested with pulse ($P_W = 40 \text{ ms}$)



			Zener Volt	age	Revers	se Current	Dynamic	Dynamic Resistance		
		V _z (V)* ¹	Test Condition	I _R (∝A)	Test Condition	r _d (Ω)	Test Condition		
Туре	Grade	Min	Max	l _z (mA)	Max	V _R (V)	Max	l _z (mA)		
HZU20	В	18.86	21.08	5	2	15.0	50	5		
	B1	18.86	19.70							
	B2	19.52	20.39							
	B3	20.21	21.08							
HZU22	В	20.88	23.17	5	2	17.0	55	5		
	B1	20.88	21.77							
	B2	21.54	22.47							
	B3	22.23	23.17							
HZU24	В	22.93	25.57	5	2	19.0	60	5		
	B1	22.93	23.96							
	B2	23.72	24.78							
	B3	24.54	25.57							
HZU27	В	25.10	28.90	2	2	21.0	70	2		
HZU30	В	28.00	32.00	2	2	23.0	80	2		
HZU33	В	31.00	35.00	2	2	25.0	80	2		
HZU36	В	34.00	38.00	2	2	27.0	90	2		

Note: 1. Tested with pulse ($P_W = 40 \text{ ms}$).



Mark Code

Туре	Grade	Mark No.	Туре	Grade	Mark No.	Туре	Grade	Mark No.
HZU2.0	В	2 · 0	HZU6.2	B1	6 · 2	HZU13	B1	13.
HZU2.2	В	2 · 2		B2	6 · 2		B2	13.
HZU2.4	В	2 · 4		B3	6 · 2		B3	13.
HZU2.7	B1	2 · 7	HZU6.8	B1	6 · 8	HZU15	B1	1 5 ·
	B2	2 · 7		B2	6 · 8		B2	1 5 ·
HZU3.0	B1	3 · 0		B3	6 · 8		B3	1 5 ·
	B2	3 · 0	HZU7.5	B1	7 · 5	HZU16	B1	1 6 ·
HZU3.3	B1	3 · 3		B2	7 · 5		B2	1 6 ·
	B2	3 · 3		B3	7 · 5		B3	1 6 ·
HZU3.6	B1	3 · 6	HZU8.2	B1	8 · 2	HZU18	B1	1 8 ·
	B2	3 · 6		B2	8 · 2		B2	1 8 ·
HZU3.9	B1	3 · 9		B3	8 · 2		B3	1 8 ·
	B2	3 · 9	HZU9.1	B1	9 · 1	HZU20	B1	20.
HZU4.3	B1	4 · 3		B2	9 · 1		B2	20.
	B2	4 · 3		B3	9 · 1		B3	20.
	B3	4 · 3	HZU10	B1	10.	HZU22	B1	22.
HZU4.7	B1	4 · 7		B2	10.		B2	22.
	B2	4 · 7		B3	10.		B3	22.
	B3	4 · 7	HZU11	B1	11.	HZU24	B1	24.
HZU5.1	B1	5 · 1		B2	11.		B2	24.
	B2	5 · 1		B3	11.		B3	24.
	B3	5 · 1	HZU12	B1	12.	HZU27	В	27.
HZU5.6	B1	5 · 6		B2	12.	HZU30	В	30.
	B2	5 · 6		B3	12.	HZU33	В	33.
	B3	5 · 6		•		HZU36	В	36.
Notes: 1. I	Example of	Marking						
(1)	One grade ty	pe (B)	(2) Two grade t	ype (B1,B2)	., -	ade type (B1,B2,B	,	
Щ	2•0 🔲 🛛	30•]] HZU30B	□ 3•0 □ HZU3.0B1	3•0 HZU3.0B2	HZU4.3B1			
			from P1 min to					

2. The grade B type includes from B1 min. to B3 (or B2) max.

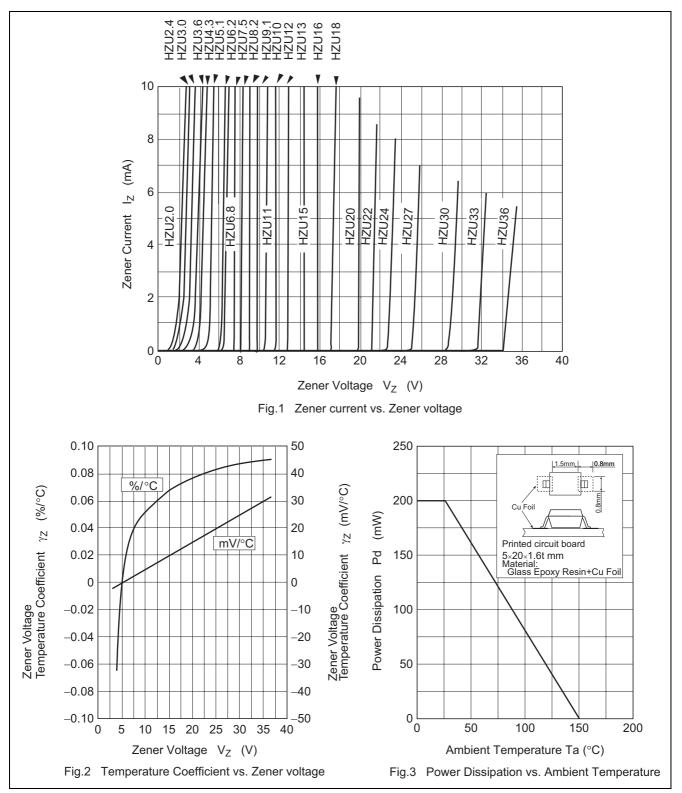
3. B grade is standard and has better delivery, these are marked one of B1, B2, B3.

4. Type No. is as follows; HZU2.0B, HZU2.2B, ••• HZU36B. (B grade)

5. Type No. is as follows; HZU2.7B1, HZU2.7B2, ••• HZU24B3. (B 1, B2, B3 grade)



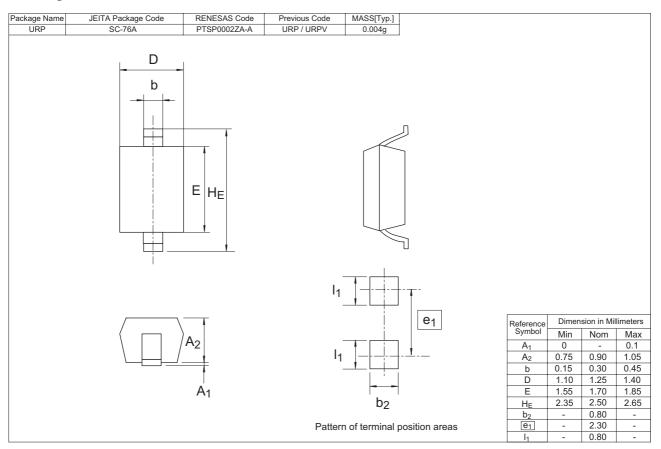
Main Characteristic



Rev.9.00 Jul 06, 2006 page 6 of 7



Package Dimensions





Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs! 1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

- Notes regarding these materials
 1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.
 2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
 3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein.
 The information described here may contain technical inaccuracies or typographical errors. Renesas Technology Corp. asy denotes any damage, liability, or other loss rising from these inaccuracies or errors. Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (http://www.renesas.com).
 4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to

- Nonine page (intp://www.renessas.com).
 4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or ther loss resulting from the information contained herein.
 5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- use. 6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials. 7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination. Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited. 8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.



RENESAS SALES OFFICES

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc. 450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

http://www.renesas.com